

2SK778



2052A

N-Channel MOS
Silicon Field-Effect Transistor

T-39-07

Very High Speed Switching Applications

©2562

Features

- Low ON resistance, very high-speed switching

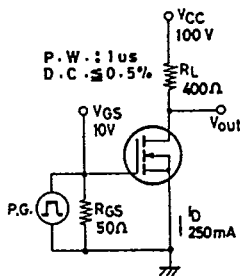
Absolute Maximum Ratings at Ta=25°C

			unit
Drain to Source Voltage	V _{DSS}	250	V
Gate to Source Voltage	V _{GSS}	±20	V
Drain Current (D.C)	I _D	500	mA
Drain Current (pulse)	I _{D peak}	1	A
Allowable Power Dissipation	P _D Tc=25°C	10	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

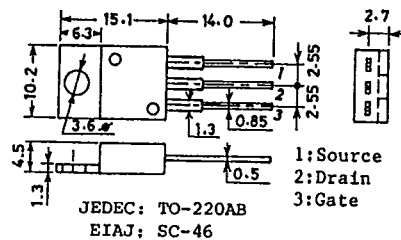
Electrical Characteristics at Ta=25°C

			min	typ	max	unit
D-S Breakdown Voltage	V _{DSS}	I _D =1mA, V _{GS} =0	250			V
D-S Cutoff Current	I _{DSS}	V _{DS} =250V, V _{GS} =0			100	uA
G-S Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0			±100	nA
G-S Cutoff Current	I _{GS(off)}	V _{DS} =10V, I _D =1mA	1.5		4.0	V
Forward Transfer Admittance	Y _{fs}	V _{DS} =10V, I _D =250mA	100	250		mS
Saturation Resistance	R _{DS(on)}	I _D =250mA, V _{GS} =10V		6	9	ohm
Input Capacitance	c _{iss}	V _{DS} =20V, f=1MHz		60		pF
Output Capacitance	c _{oss}	V _{DS} =20V, f=1MHz		20		pF
Reverse Transfer Capacitance	c _{rss}	V _{DS} =20V, f=1MHz		4		pF
Turn-on Delay Time	t _{on}	I _D =250mA, V _{GS} =10V		25		ns
Turn-off Delay Time	t _{off}	I _D =250mA, V _{GS} =10V		60		ns

Switching Time Test Circuit



Case Outline 2052A (unit:mm)

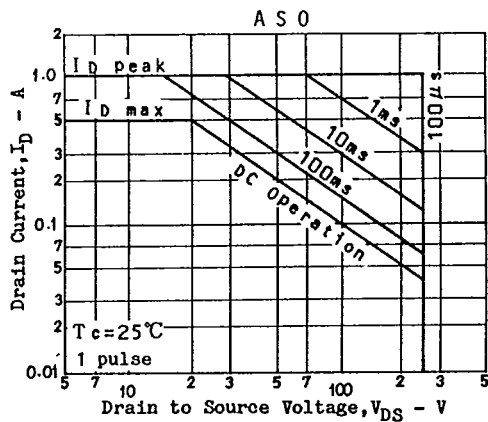
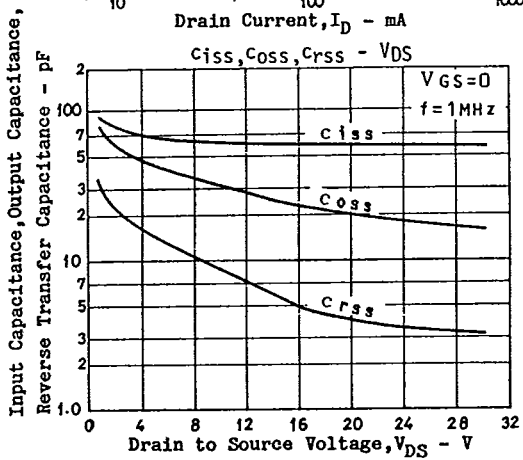
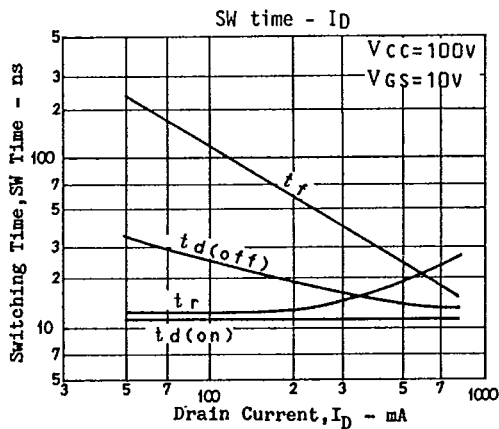
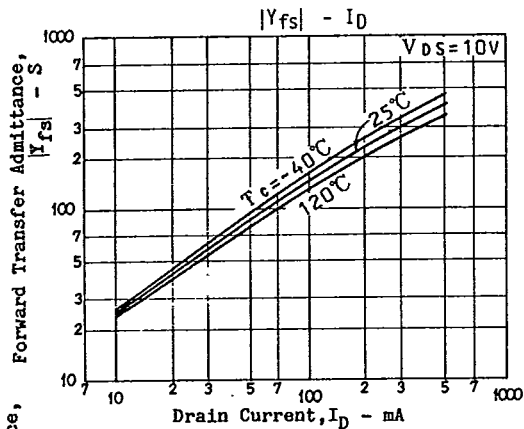
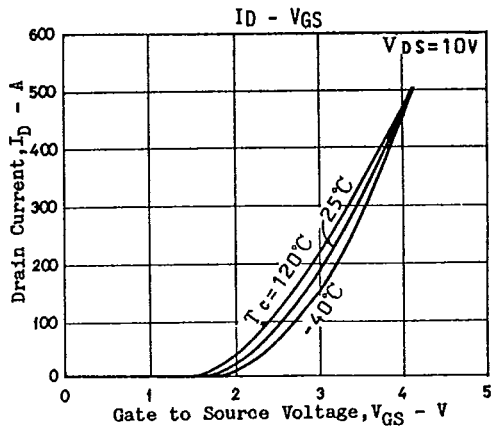
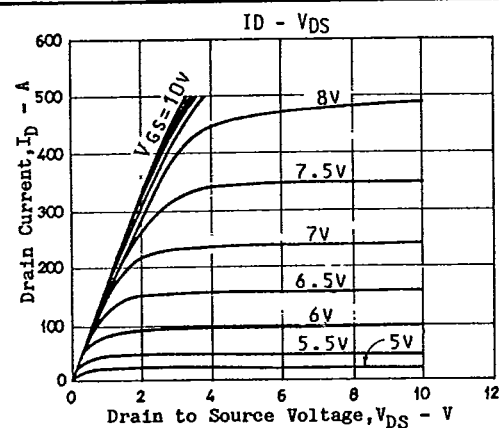


Note: Be carefull in handling the 2SK778 because it has no protect diode between gate and source.

4277TA, TS No.2562-1/2

2SK778

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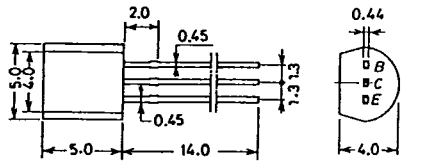
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CASE OUTLINES AND ATTACHMENTS

- All of Sanyo Transistor case outlines are illustrated below.
- All dimensions are in mm, and dimensions which are not followed by min. or max. are represented by typical values.
- No marking is indicated.

Case Outline-[2003A]

unit:mm

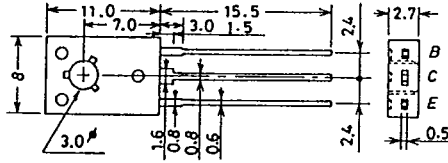


JEDEC: TO-92
EIAJ: SC-43
SANYO: NP

B. Base
C. Collector
E. Emitter

Case Outline-[2009A]

unit:mm

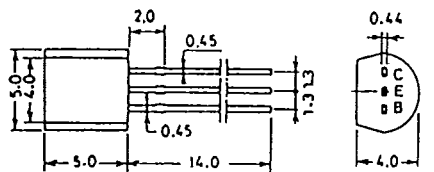


JEDEC: TO-126

B: Base
C: Collector
E: Emitter

Case Outline-[2004A]

unit:mm

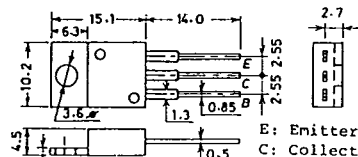


JEDEC: TO-92
EIAJ: SC-43
SANYO: NP

C. Collector
E. Emitter
B. Base

Case Outline-[2010A]

unit:mm

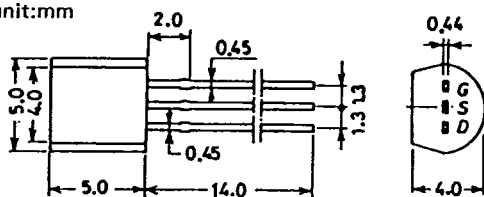


JEDEC: TO-220AB
EIAJ: SC-46

E: Emitter
C: Collector
B: Base

Case Outline-[2005A]

unit:mm

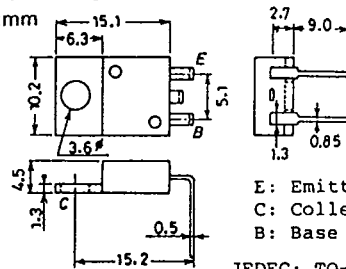


JEDEC: TO-92
EIAJ: SC-43
SANYO: NP

G: Gate
S: Source
D: Drain

Case Outline-[2012]

unit:mm

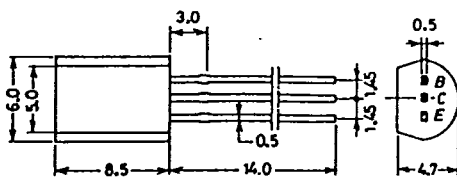


JEDEC: TO-220AA
EIAJ: SC-45

E: Emitter
C: Collector
B: Base

Case Outline-[2006A]

unit:mm

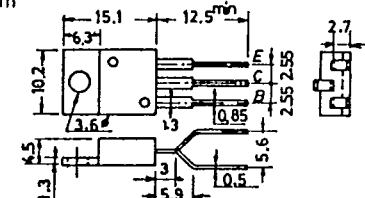


EIAJ: SC-51
SANYO: MP

B: Base
C: Collector
E: Emitter

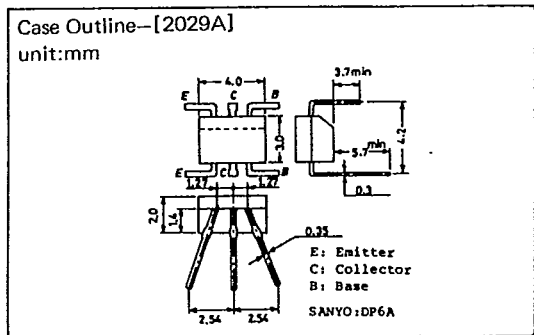
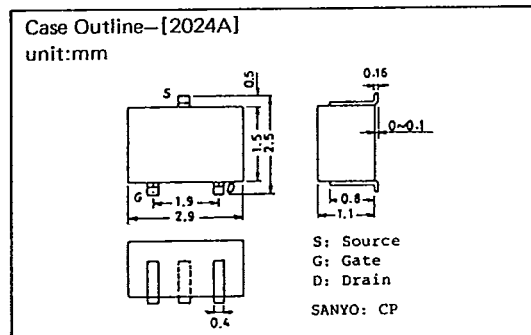
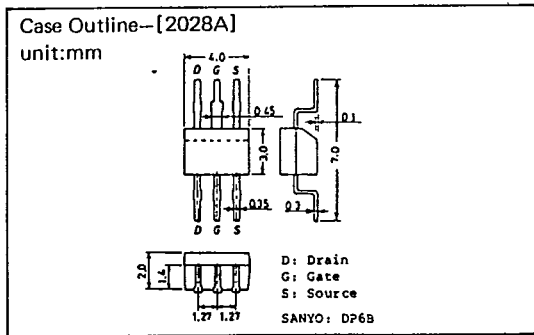
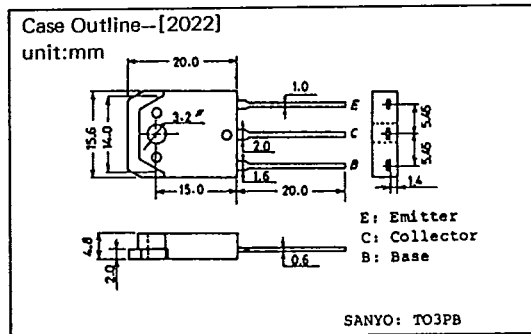
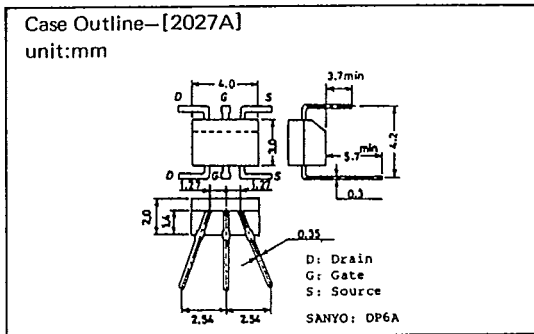
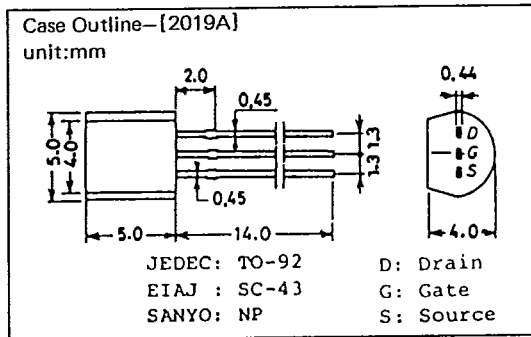
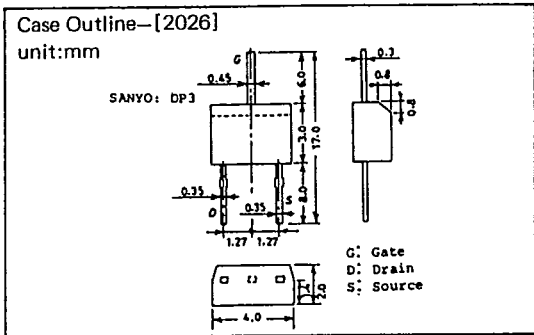
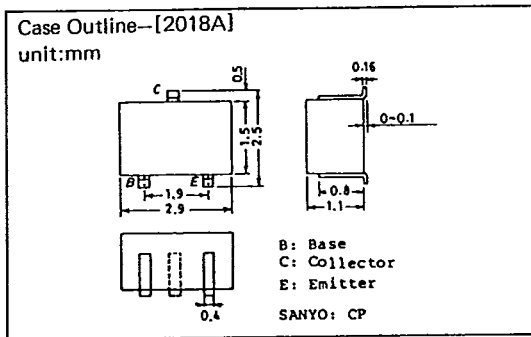
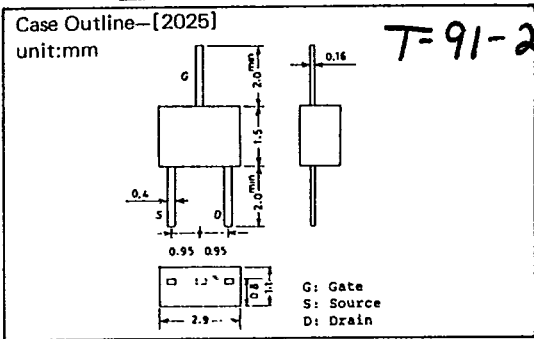
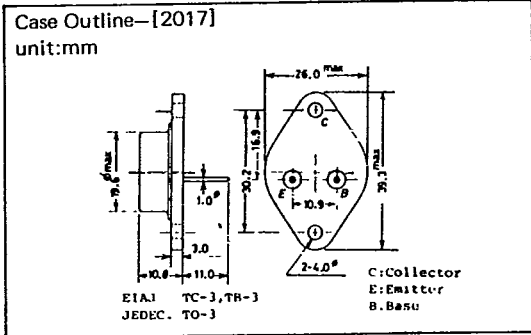
Case Outline-[2013]

unit:mm



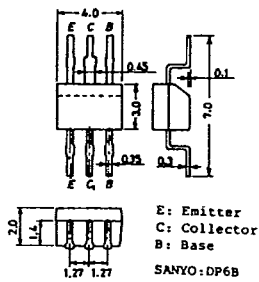
JEDEC TO-220

B: Base
C: Collector
E: Emitter

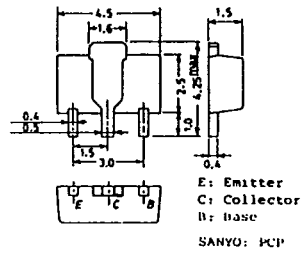


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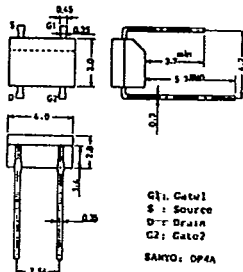
Case Outline—[2030A]
unit:mm



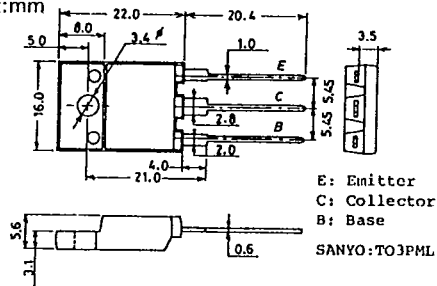
Case Outline—[2038]
unit:mm



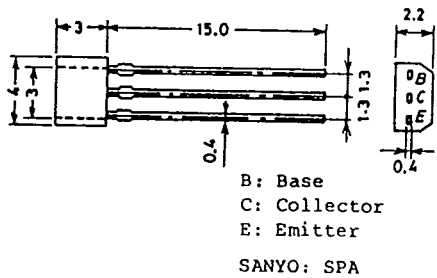
Case Outline—[2031A]
unit:mm



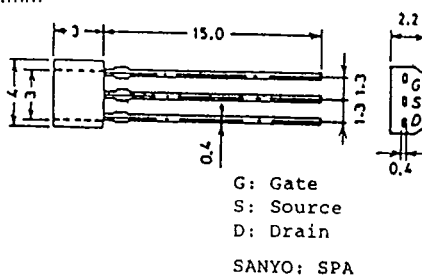
Case Outline—[2039]
unit:mm



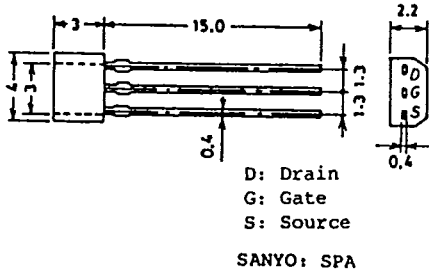
Case Outline—[2033]
unit:mm



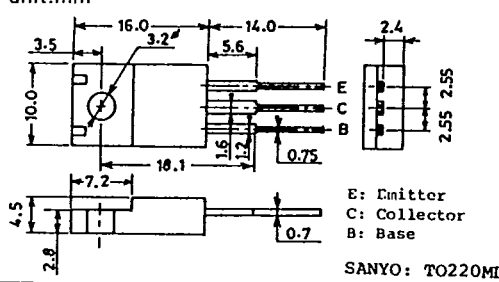
Case Outline—[2040]
unit:mm



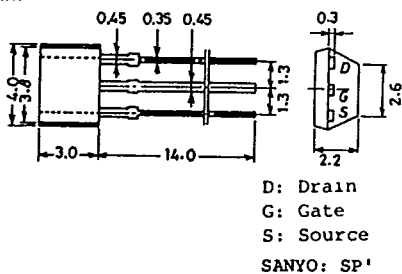
Case Outline—[2034]
unit:mm



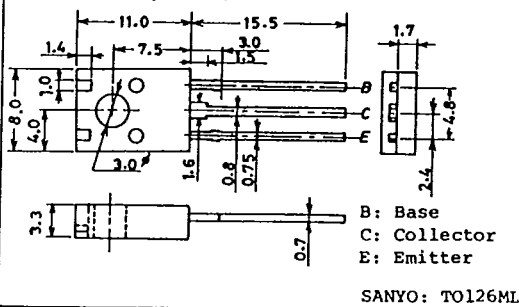
Case Outline—[2041]
unit:mm



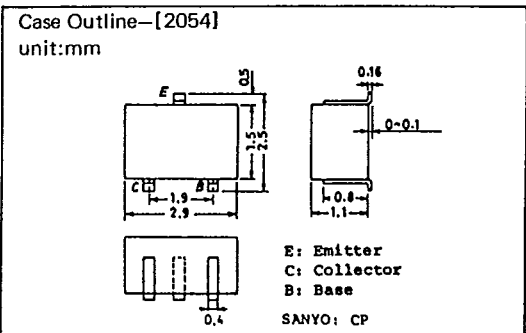
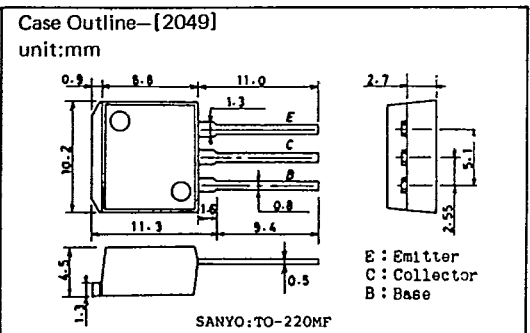
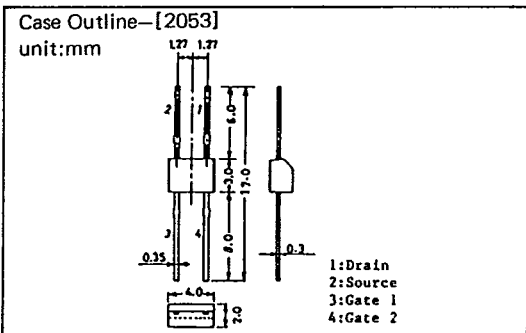
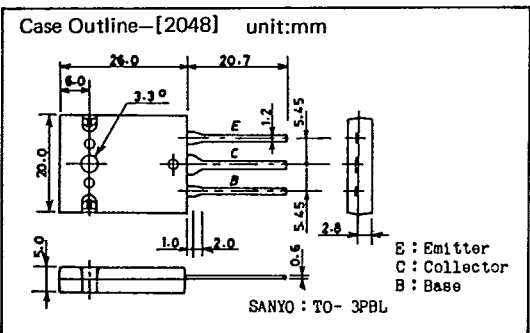
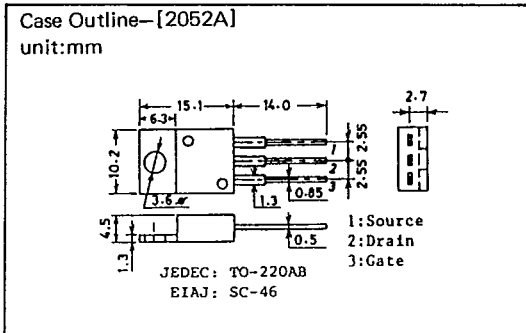
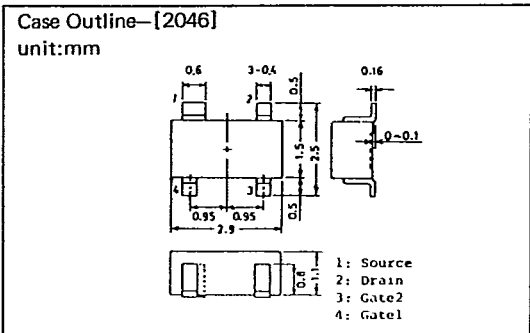
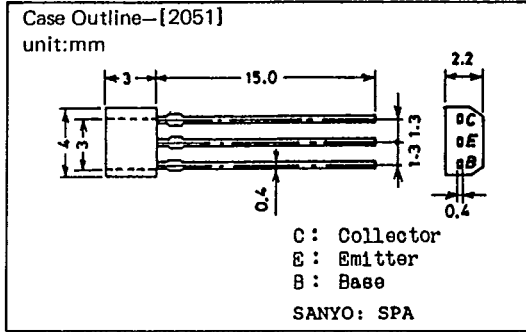
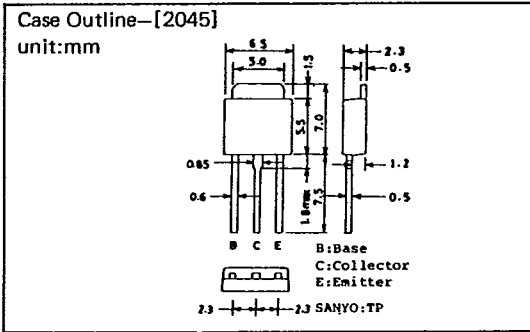
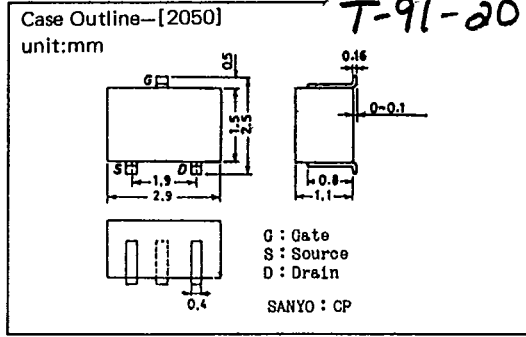
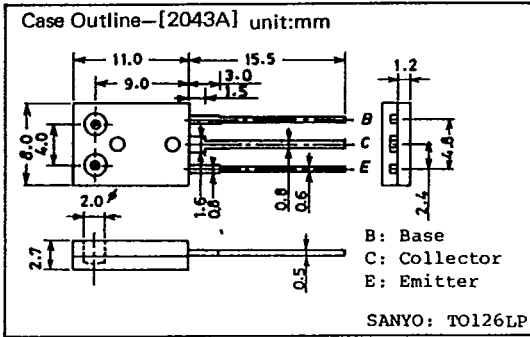
Case Outline—[2037]
unit:mm



Case Outline—[2042A] unit:mm



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